imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Thyristor Module

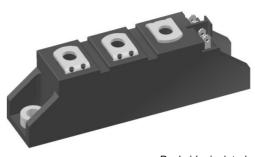
MCC19-14io1B

V_{RRM}	<i>=</i> 2x 1400 V		
I _{tav}	=	18 A	
V _T	=	1.57 V	

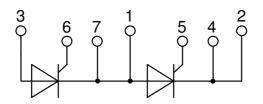
Phase leg

Part number

MCC19-14io1B



Backside: isolated **E**72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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MCC19-14io1B

Thyristo				1	Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{vJ} = 25^{\circ}C$			1500	\ \
V _{RRM/DRM}	max. repetitive reverse/forward bl		$T_{VJ} = 25^{\circ}C$			1400	١
R/D	reverse current, drain current	V _{R/D} = 1400 V	$T_{vJ} = 25^{\circ}C$			100	μ/
		V _{R/D} = 1400 V	$T_{vJ} = 125^{\circ}C$			3	m/
V _T	forward voltage drop	$I_{T} = 40 \text{ A}$	$T_{vJ} = 25^{\circ}C$			1.56	١
		I _T = 80 A				2.05	١
		$I_{T} = 40 \text{ A}$	$T_{VJ} = 125^{\circ}C$			1.57	١
		I _T = 80 A				2.29	١
ITAV	average forward current	$T_c = 85^{\circ}C$	$T_{vJ} = 125^{\circ}C$			18	ŀ
I _{T(RMS)}	RMS forward current	180° sine				28	ļ
V _{T0}	threshold voltage		T _{vJ} = 125°C			0.85	١
r _T	slope resistance } for power lo	oss calculation only				18	m۵
R _{thJC}	thermal resistance junction to cas	e				1.3	K/W
R _{thCH}	thermal resistance case to heatsi				0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			77	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v,l} = 45^{\circ}C$			400	ļ
•15M		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			430	ļ
		t = 10 ms; (50 Hz), sine	$T_{\rm WI} = 125^{\circ}{\rm C}$			340	
		t = 8,3 ms; (60 Hz), sine	$V_{\rm N} = 0$ V			365	,
l²t	value for fusing	t = 0.5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$\frac{v_{R} = 0.7}{T_{V,I} = 45^{\circ}C}$			800	A ² s
1-1	value for fusing					800 770	A-s A ² s
		t = 8,3 ms; (60 Hz), sine t = 10 ms; (50 Hz), sine	$V_{\rm R} = 0 V$				
			$T_{vJ} = 125 ^{\circ}C$			580	A ² 9
_	ium etiene en en etiene en	t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			555	A ² s
C,	junction capacitance	$V_{\rm R} = 400 \text{V} \text{f} = 1 \text{MHz}$	$T_{\rm VJ} = 25^{\circ}\rm C$		22	10	pF
₽ _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 125^{\circ}C$			10	W
_		t _P = 300 μs				5	W
P _{GAV}	average gate power dissipation					0.5	W
(di/dt) _{cr}	critical rate of rise of current	$T_{vJ} = 125 ^{\circ}C; f = 50 \text{Hz}$ re	•			150	A/μ
		t_{P} = 200 µs; di _G /dt =0.45 A/µs; -					
			on-repet., $I_{T} = 18 \text{ A}$				A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{vJ} = 125^{\circ}C$			1000	V/µs
		$R_{GK} = \infty$; method 1 (linear volta	ge rise)				
V _{ат}	gate trigger voltage	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			1.5	١
			$T_{vJ} = -40 ^{\circ}C$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{v_J} = 25^{\circ}C$			100	mA
			$T_{vJ} = -40 ^{\circ}\text{C}$			200	mÆ
V _{gd}	gate non-trigger voltage	$V_{\rm D} = \frac{2}{3} V_{\rm DBM}$	T _{vJ} = 125°C			0.2	١
I _{GD}	gate non-trigger current					5	mA
IL	latching current	t _p = 10 μs	$T_{vJ} = 25 ^{\circ}C$			450	m/
	-	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$					
I _H	holding current	$V_{\rm D} = 6 \text{V} \text{R}_{\rm GK} = \infty$	T _{vJ} = 25°C			200	m/
т _{gd}	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{VJ} = 25^{\circ}C$			200	μ
• gd	gate controlled delay ante	$I_{G} = 0.45 \text{ A}; \text{ di}_{G}/\text{dt} = 0.45 \text{ A}/\mu\text{s}$				2	μ
•	turn-off time	$V_{\rm g} = 0.43$ Å, $dI_{\rm g}/dI = 0.43$ Å/µs $V_{\rm g} = 100$ V; $I_{\rm T} = 20$ Å; $V = ^{2}$			150		
t _q		$v_{\rm R} = 100 v, I_{\rm T} = 20 A, V = 7$	$3 V_{\text{DRM}} I_{\text{VJ}} = 100^{-1} \text{C}$		150		μ

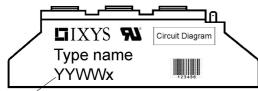
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MCC19-14io1B

Package	TO-240AA				F	Rating	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					200	Α
T _{vj}	virtual junction temperature				-40		125	°C
T _{op}	operation temperature				-40		100	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	creepage distance on surface striking distance through a	e / striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on surrac	e suiking ustance through an	terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		3000			V



Date Code

ſ	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MCC19-14io1B	MCC19-14io1B	Box	36	452858

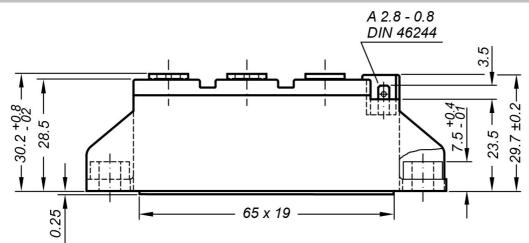
Similar Part	Package	Voltage class
MCMA25P1600TA	TO-240AA-1B	1600
MCMA35P1600TA	TO-240AA-1B	1600

Equiva	lent Circuits for	Simulation	* on die level	T _{vj} = 125 °C
	⊢R₀_−	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$\mathbf{R}_{0 \max}$	slope resistance *	16.8		mΩ

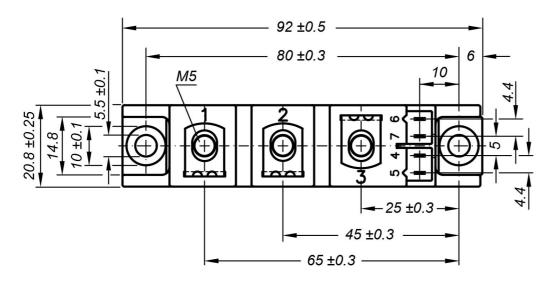
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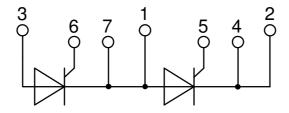
Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5) Type **ZY 200R** (R = Right for pin pair 6/7)



DC

50

1: I_{GT} , $T_{VJ} = 125^{\circ}C$ 2: I_{GT} , T_{VJ} = 25°C

3: I_{GT}, T_{VJ} = -40°C

T_{VJ} = 125°C

10¹

I_{GD}

180° sin 120°₋∟

60° Л 30° □

100

at case temperature

T_c [°C]

150

5 W 5: P_{CM} =

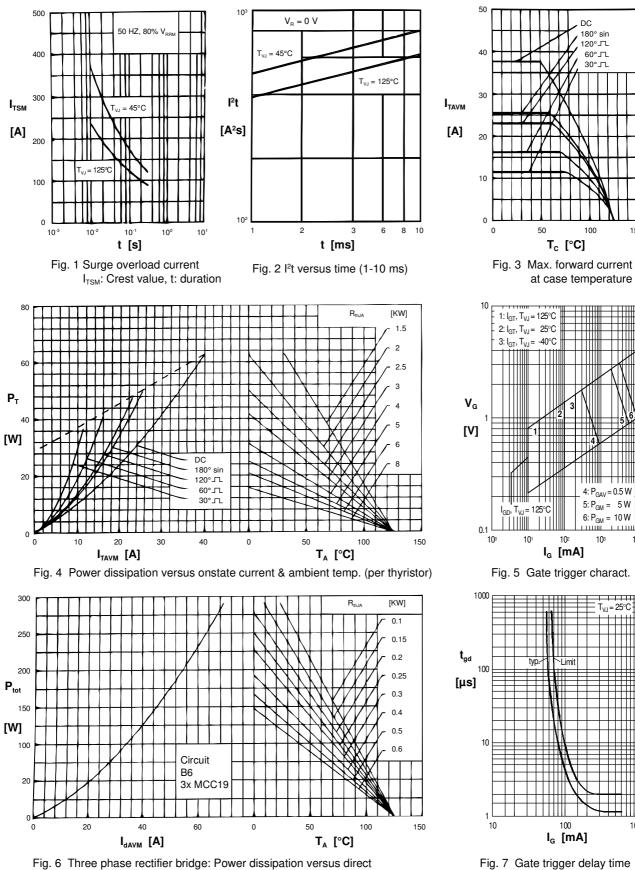
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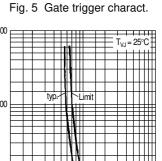
> > 104

6: P_{GM} = 10 W

10³

Thyristor





100

 I_{G} [mA]

102

 I_{G} [mA]



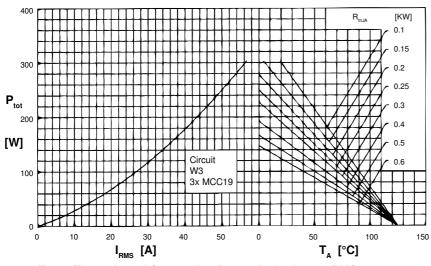


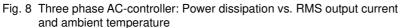
1000

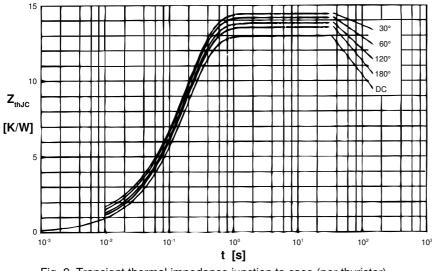
output current and ambient temperature

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Thyristor

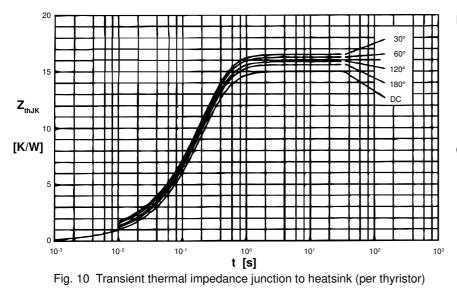






R_{thJ}	_{ic} for vari	ous conduction angles d:
	d R _t	_{hJC} [K/W]
	DC	1.30
	180°	1.35
	120°	1.39
	60°	1.42
	30°	1.45
Co	nstants fo	or Z _{thJC} calculation:
i	R _{thi} [K/W	′] t _i [s]
1	0.018	0.0033
2	0.041	0.0216
3	1.241	0.1910





 $R_{_{thJK}}$ for various conduction angles d: d $\mathsf{R}_{\mathsf{thJK}}$ [K/W] DC 1.50 180° 1.55 120° 1.59 60° 1.62 30° 1.65 Constants for $\boldsymbol{Z}_{_{thJK}}$ calculation: i R_{thi} [K/W] t_i [s] 1 0.018 0.0033 0.0216 0.041 2 3 0.1910 1.241 4 0.200 0.4600

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